



GP
ELECTRONICS

GPT018N03LNC
30V N-Channel MOSFET

Product Summary

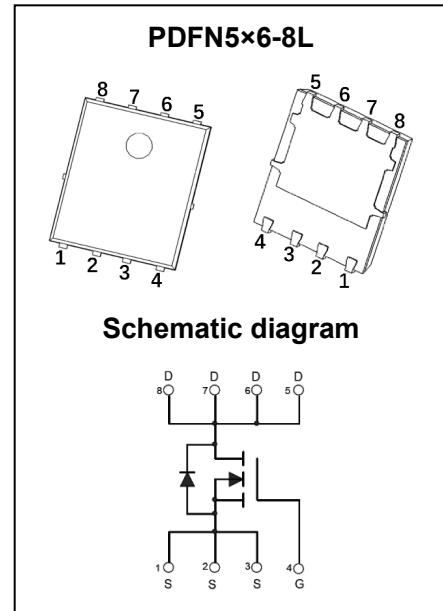
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	1.7mΩ@10V	120A
	2.4mΩ@4.5V	

Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Power Switching Application



MARKING:



T018N03L = Device Code

XX = Date Code

Solid Dot = Green Indicator

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

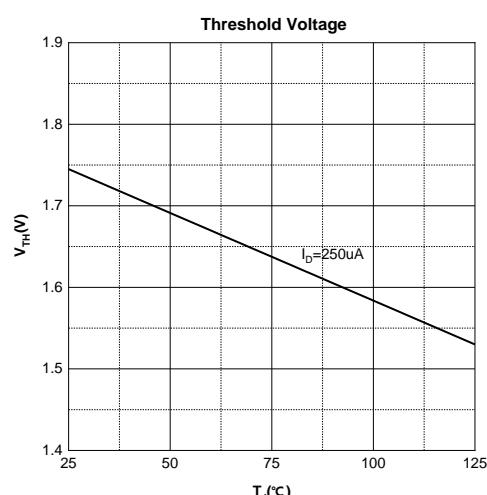
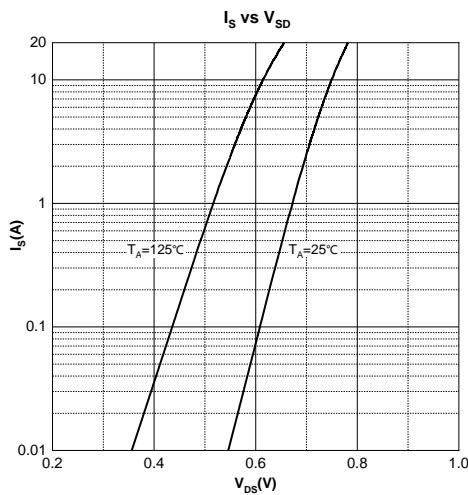
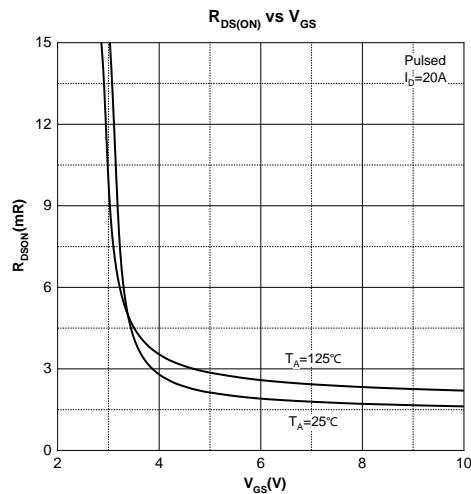
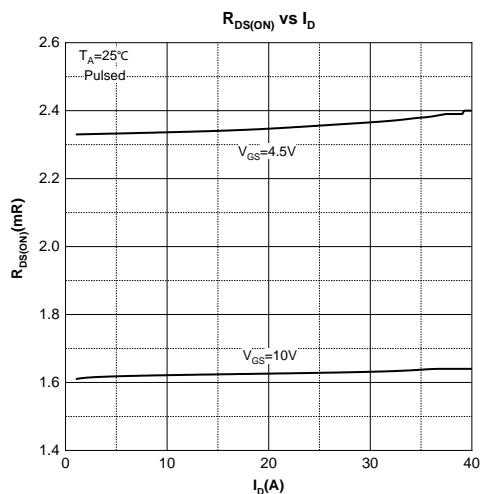
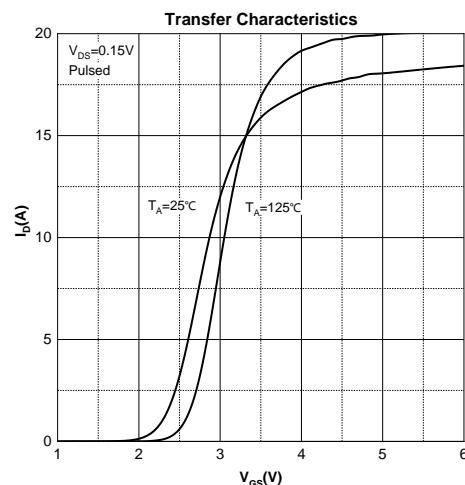
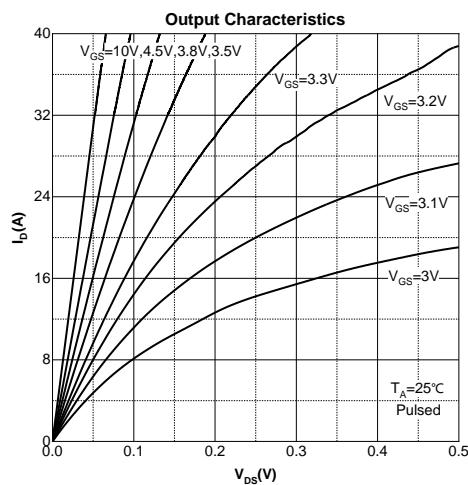
Parameter	Symbol	Value	Unit
Drain - Source Voltage	V_{DS}	30	V
Gate - Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	I_D	120	A
	I_D	84	A
Pulsed Drain Current ²	I_{DM}	480	A
Single Pulsed Avalanche Current ³	I_{AS}	41	A
Single Pulsed Avalanche Energy ³	E_{AS}	420	mJ
Power Dissipation ⁵	P_D	78	W
Thermal Resistance from Junction to Ambient ⁶	$R_{\theta JA}$	50	°C/W
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.6	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

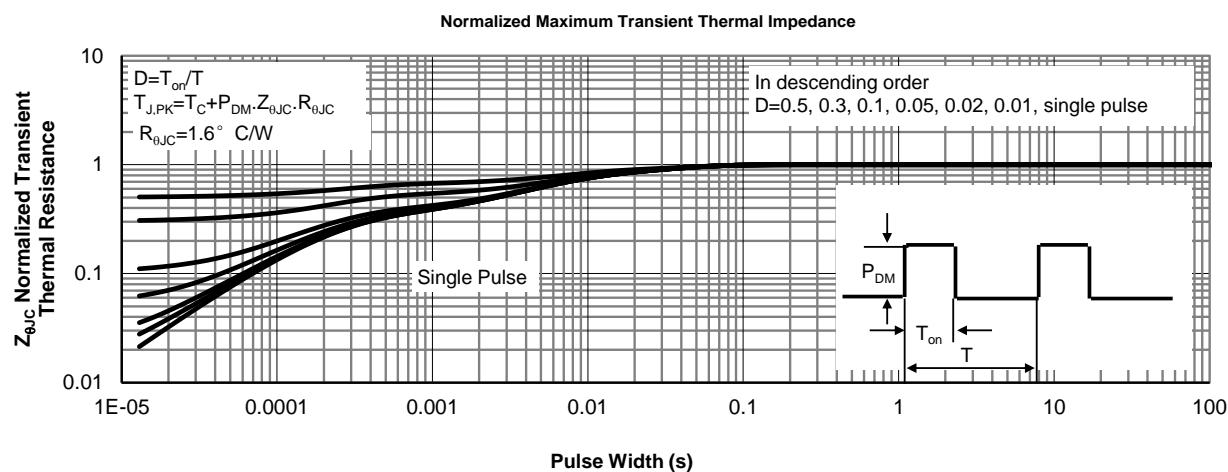
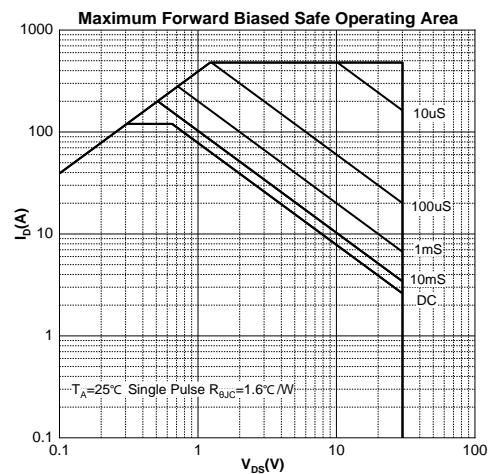
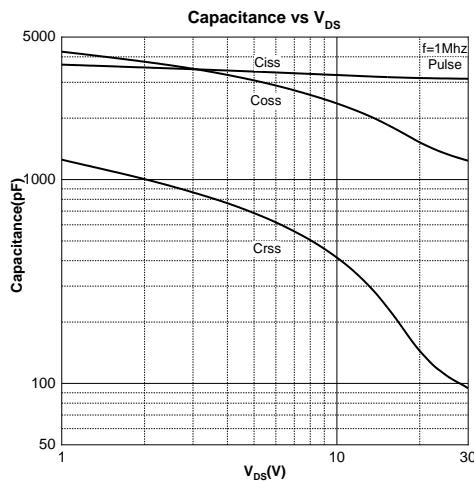
MOSFET ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

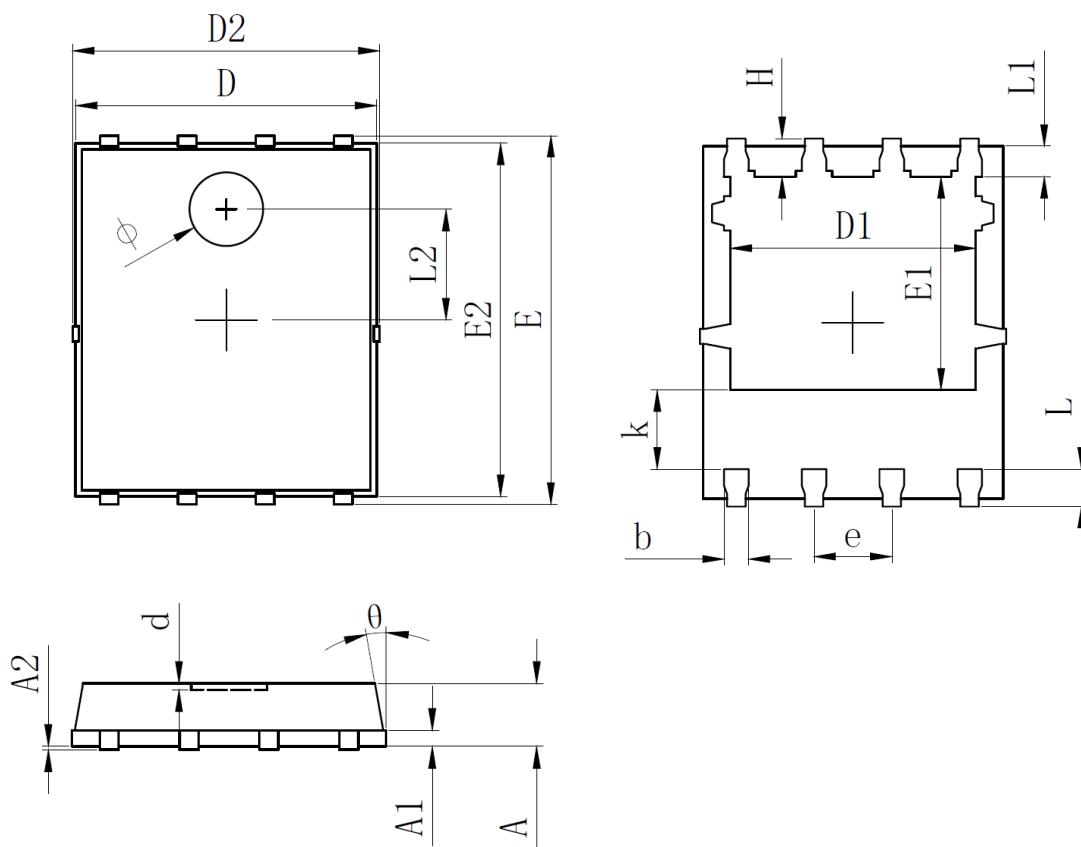
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 100	nA
On Characteristics⁴						
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	1.0	1.7	3.0	V
Drain-source On-resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10\text{V}, I_D = 20\text{A}$		1.7	2.2	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5\text{V}, I_D = 10\text{A}$		2.4	3.2	
Forward Transconductance	g_{FS}	$V_{\text{DS}} = 5\text{V}, I_D = 20\text{A}$		100		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 15\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		3114		pF
Output Capacitance	C_{oss}			1889		
Reverse Transfer Capacitance	C_{rss}			216		
Gate Resistance	R_g	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		3.3		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{\text{DS}} = 15\text{V}, V_{\text{GS}} = 10\text{V}, I_D = 20\text{A}$		58		nC
Gate-source Charge	Q_{gs}			8.7		
Gate-drain Charge	Q_{gd}			11.9		
Turn-on Delay Time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = 15\text{V}, V_{\text{GS}} = 10\text{V}, R_L = 0.75\Omega, R_G = 3\Omega$		10		ns
Turn-on Rise Time	t_r			5		
Turn-off Delay Time	$t_{\text{d}(\text{off})}$			83		
Turn-off Fall Time	t_f			20		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{\text{GS}} = 0\text{V}, I_s = 10\text{A}$			1.2	V

Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu\text{s}$, duty cycle $\leq 1\%$.
- 3.E_{AS} condition: $V_{\text{DD}} = 25\text{V}, V_{\text{GS}} = 10\text{V}, L = 0.5\text{mH}, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(\text{MAX})} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics




PDFN5x6-8L Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.254REF		0.010REF	
A2	0.000	0.050	0.000	0.002
D	4.824	4.976	0.190	0.196
D1	3.910	4.110	0.154	0.162
D2	4.924	5.076	0.194	0.200
E	5.924	6.076	0.233	0.239
E1	3.375	3.575	0.133	0.141
E2	5.674	5.826	0.223	0.229
b	0.350	0.450	0.014	0.018
e	1.270TYP		0.050TYP	
L	0.534	0.686	0.021	0.027
L1	0.424	0.576	0.017	0.023
k	1.190	1.390	0.047	0.055
H	0.549	0.701	0.022	0.028
θ	8°	12°	8°	12°
Φ	1.100	1.300	0.043	0.051
d	-	0.100	-	0.004